Please amend the subject application as follows:

IN THE CLAIMS:

Please cancel claim 26 without prejudice, and accept amended claim 25 and new claim 31 as follows:

1. (previously presented) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode, comprising a first upper electrode and a second upper electrode, formed on the dielectric film, wherein:

the first upper electrode is formed by physical vapor deposition without bias power applied to the semiconductor substrate and the second upper electrode is formed by chemical vapor deposition.

2. (original) The capacitor of claim 1, wherein the upper electrode is made of one selected from the group consisting of titanium nitride, tantalum nitride, tungsten nitride, ruthenium, platinum, iridium, and a combination thereof.

3. (canceled)

4. (previously presented) The capacitor of claim 1, wherein the first upper electrode and the second upper electrode are sequentially stacked.

5. - 22. (canceled)

23. (previously presented) A capacitor comprising:

a lower electrode formed on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film, wherein:

the upper electrode is formed by physical vapor deposition and one of chemical vapor deposition and atomic layer deposition, and

the upper electrode includes a first upper electrode formed by the physical vapor deposition without bias power applied to the semiconductor substrate and a second upper electrode formed by one of the chemical vapor deposition and the atomic layer deposition.

24. (canceled)

25. (currently amended) A capacitor comprising:

a lower electrode formed in a concave hole and on a semiconductor substrate;

a dielectric film stacked on the lower electrode; and

an upper electrode formed on the dielectric film, wherein:

the upper electrode includes a first upper electrode formed by physical vapor deposition without bias power applied to the semiconductor substrate to form the first upper electrode on a sidewall of the concave hole.

26. (canceled)

27. (previously presented) The capacitor of claim 25, wherein the upper electrode further includes a second upper electrode formed by chemical vapor deposition.

28. (previously presented) The capacitor of claim 1, wherein the capacitor is a concave-type capacitor.

29. (previously presented) The capacitor of claim 23, wherein the capacitor is a concave-type capacitor.

30. (previously presented) The capacitor of claim 25, wherein the capacitor is a concave-type capacitor.

31. (new) The capacitor of claim 27, further comprising an anti-reflective layer formed on the second upper electrode.